

**ATTENTION**  
OBSERVE PRECAUTIONS  
FOR HANDLING  
ELECTROSTATIC  
SENSITIVE  
DEVICES

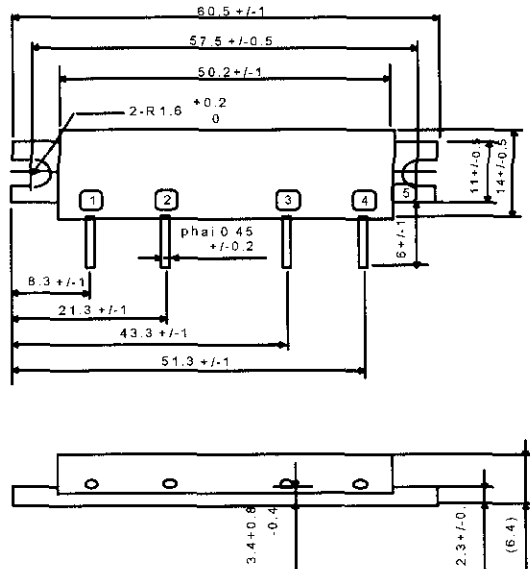
## MITSUBISHI RF POWER MODULE

# M68701M

Silicon MOS FET Power Amplifier, 860-915MHz 6W FM /Digital Mobile

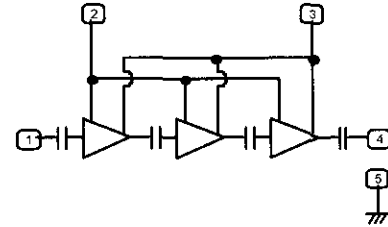
### OUTLINE DRAWING

Dimensions in mm



H 11

### BLOCK DIAGRAM



PIN:

- ① Pin : RF INPUT
- ② VGG : GATE BIAS SUPPLY
- ③ VDD : DRAIN BIAS SUPPLY
- ④ Po : RF OUTPUT
- ⑤ GND : FIN

### MAXIMUM RATINGS (Tc=25deg C UNLESS OTHERWISE NOTED)

| SYMBOL | PARAMETER                  | CONDITIONS                  | RATINGS     | UNIT   |
|--------|----------------------------|-----------------------------|-------------|--------|
| VDD    | SUPPLY VOLTAGE             | VGG<5V, ZG=ZL=50 ohms       | 17          | V      |
| VGG    | GATE BIAS VOLTAGE          |                             | 5.5         | V      |
| Pin    | INPUT POWER                | f=860-915MHz, ZG=ZL=50 ohms | 10          | mW     |
| Po     | OUTPUT POWER               | f=860-915MHz, ZG=ZL=50 ohms | 10          | W      |
| Tc(OP) | OPERATION CASE TEMPERATURE | f=860-915MHz, ZG=ZL=50 ohms | -30 to +100 | deg. C |
| Tstg   | STORAGE TEMPERATURE        |                             | -40 to +110 | deg. C |

Note: Above parameters are guaranteed independently.

### ELECTRICAL CHARACTERISTICS (Tc=25deg. C, Zg=Zl=50 ohms UNLESS OTHERWISE NOTED)

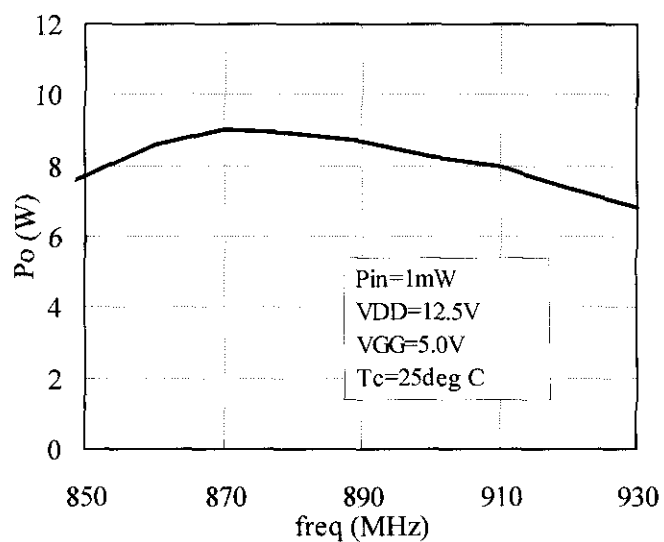
| SYMBOL     | PARAMETER           | TEST CONDITIONS                                                      | LIMITS                    |     | UNIT |
|------------|---------------------|----------------------------------------------------------------------|---------------------------|-----|------|
|            |                     |                                                                      | MIN                       | MAX |      |
| f          | FREQUENCY RANGE     |                                                                      | 860                       | 915 | MHz  |
| Po         | OUTPUT POWER        | VDD=12.5V, VGG=5V, Pin=1mW                                           | 6                         |     | W    |
| Efficiency | TOTAL EFFICIENCY    | VDD=12.5V,                                                           | 35                        |     | %    |
| 2fo        | 2nd HARMONIC        | Pout=6W (VGG adjust)                                                 |                           | -30 | dBc  |
| VSWR in    | INPUT VSWR          | Pin=1mW                                                              |                           | 4   | -    |
| -          | LOAD VSWR TOLERANCE | VDD=15.2V, Pin=1mW, Po=6W (VGG adjust)<br>ZG=50 ohms, LOAD VSWR=20:1 | No degradation or destroy |     | -    |

ABOVE PARAMETERS, RATINGS, LIMITS AND CONDITIONS ARE SUBJECT TO CHANGE.

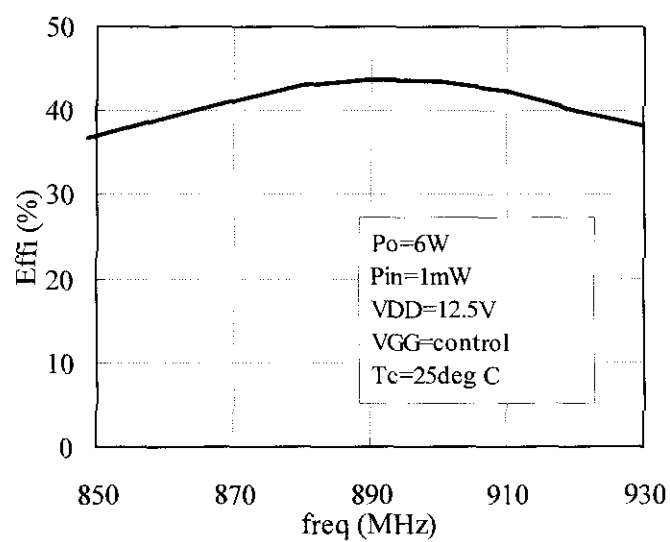
Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

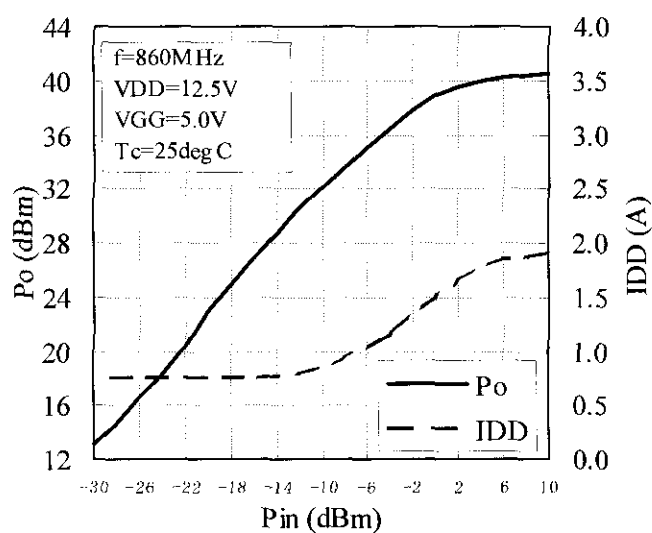
Po vs. freq



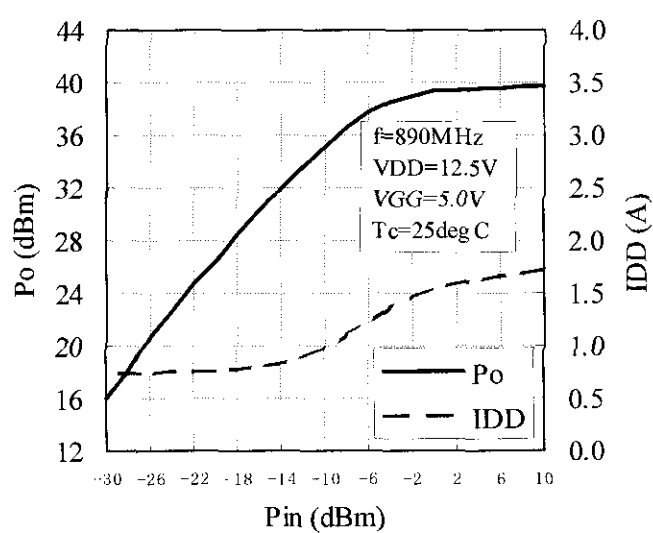
Efficiency vs. freq



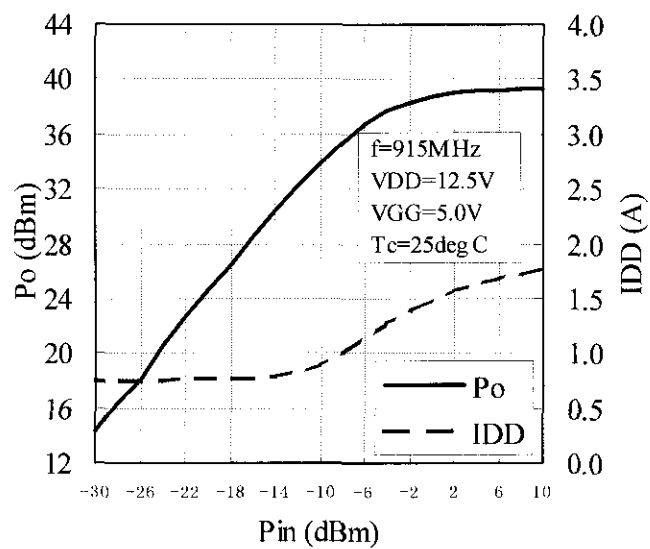
Po, IDD vs. Pin (860MHz)



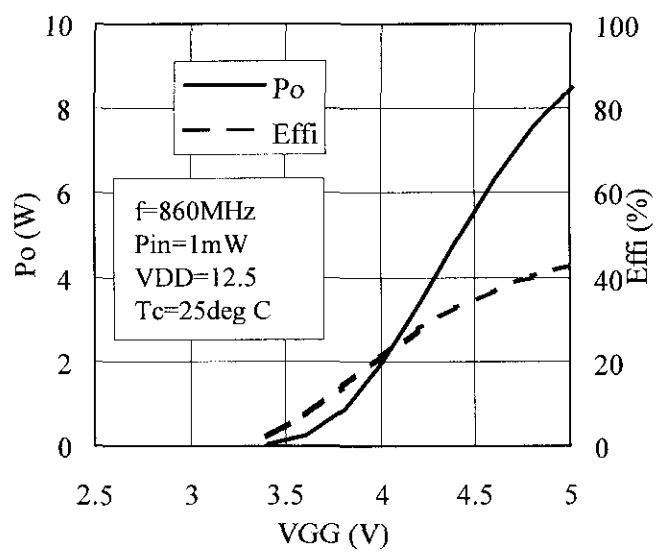
Po, IDD vs. Pin (890MHz)



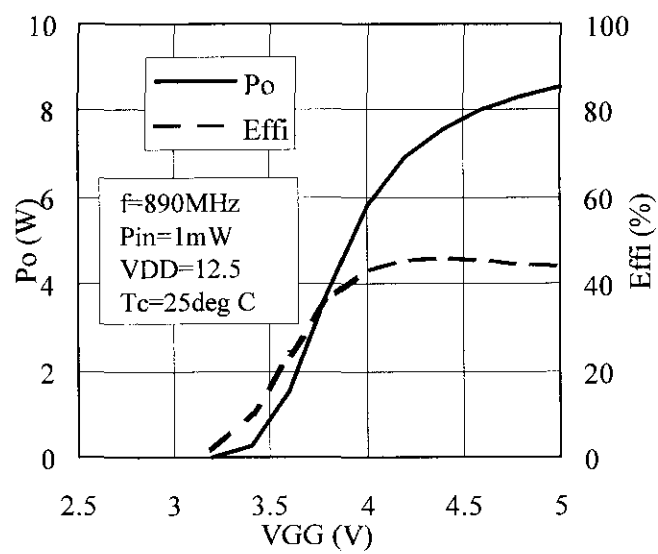
Po, IDD vs. Pin (915MHz)



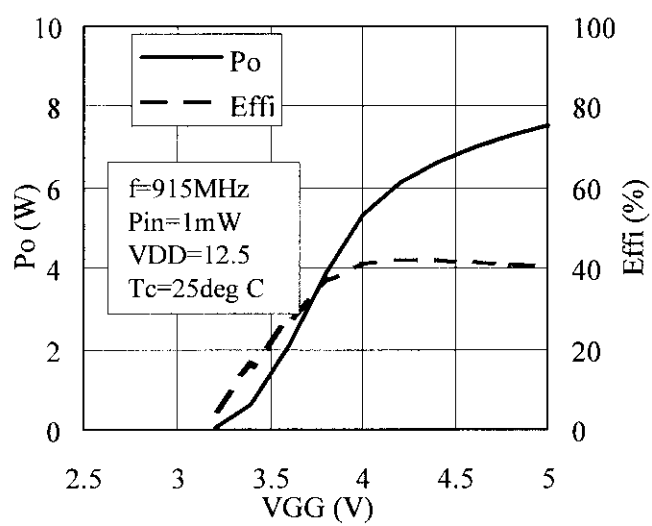
Po, Effi vs. VGG (860MHz)



Po, Effi vs. VGG (890MHz)



Po, Effi vs. VGG (915MHz)



Po vs. VDD

